



VP11A



P-Channel Enhancement-Mode Vertical DMOS FETs

Ordering Information Standard Commercial Devices

BV _{DSS} / BV _{DGS}	R _{DS(ON)} (max)	I _{D(ON)} (min)	Order Number / Package		
			TO-39	TO-220	DICE†
-60V	2Ω	-5A	VP1106N2	VP1106N5	VP1106ND
-100V	2Ω	-5A	VP1110N2	VP1110N5	VP1110ND

† MIL visual screening available

High Reliability Devices

See pages 5-4 and 5-5 for MILITARY STANDARD Process Flows and Ordering Information.

Features

- Free from secondary breakdown
- Low power drive requirement
- Ease of paralleling
- Low C_{ISS} and fast switching speeds
- Excellent thermal stability
- Integral Source-Drain diode
- High input impedance and high gain
- Complementary N- and P-channel devices

Applications

- Motor control
- Converters
- Amplifiers
- Switches
- Power supply circuits
- Driver (relays, hammers, solenoids, lamps, memories, displays, bipolar transistors, etc.)

Absolute Maximum Ratings

Drain-to-Source Voltage	BV _{DSS}
Drain-to-Gate Voltage	BV _{DGS}
Gate-to-Source Voltage	± 20V
Operating and Storage Temperature	-55°C to +150°C
Soldering Temperature*	300°C

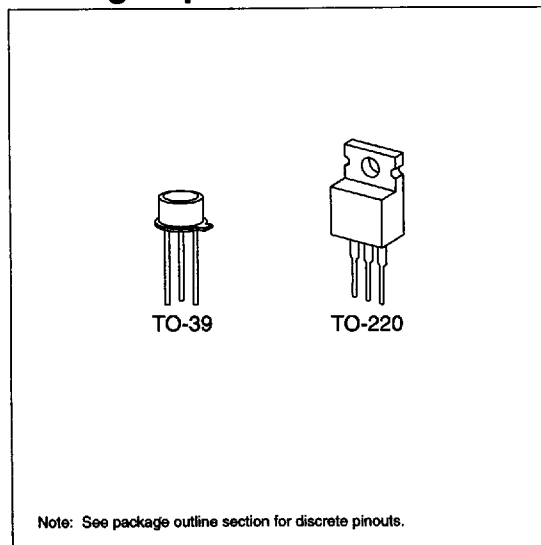
* Distance of 1.6 mm from case for 10 seconds.

Advanced DMOS Technology

These enhancement-mode (normally-off) transistors utilize a vertical DMOS structure and Supertex's well-proven silicon-gate manufacturing process. This combination produces devices with the power handling capabilities of bipolar transistors and with the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, these devices are free from thermal runaway and thermally-induced secondary breakdown.

Supertex vertical DMOS FETs are ideally suited to a wide range of switching and amplifying applications where high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.

Package Options



Note: See package outline section for discrete pinouts.

Thermal Characteristics

61E D ■ 8773295 0003254 072 ■ STX

Package	I_D (continuous)*	I_D (pulsed)	Power Dissipation @ $T_C = 25^\circ\text{C}$	θ_{JA} $^\circ\text{C/W}$	θ_{JC} $^\circ\text{C/W}$	I_{DR}^*	I_{DRM}
TO-39	-1.5A	-7A	6W	125	20.8	-1.5A	-7A
TO-220	-4.0A	-12A	45W	70	2.78	-4A	-12A

* I_D (continuous) is limited by max rated T_J .

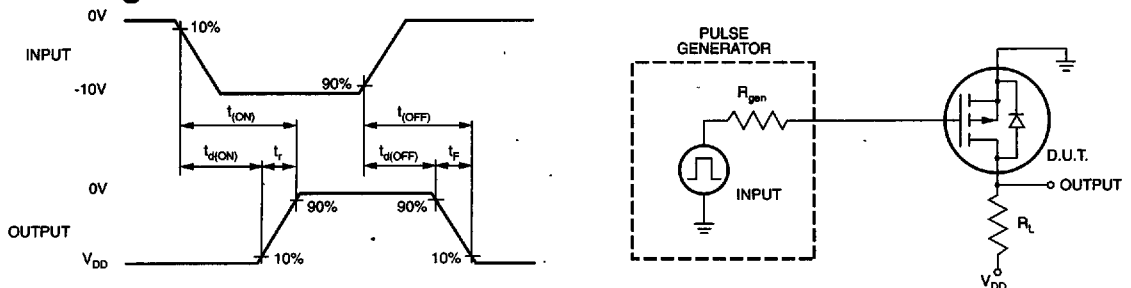
Electrical Characteristics (@ 25°C unless otherwise specified)

Symbol	Parameter	Min	Typ	Max	Unit	Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	VP1110	-100		V	$I_D = -5\text{mA}, V_{GS} = 0\text{V}$
		VP1106	-60			
$V_{GS(th)}$	Gate Threshold Voltage	-1.5		-3.5	V	$V_{GS} = V_{DS}, I_D = -5\text{mA}$
$\Delta V_{GS(th)}$	Change in $V_{GS(th)}$ with Temperature		4.0		mV/°C	$I_D = -5\text{mA}, V_{GS} = V_{DS}$
I_{GSS}	Gate Body Leakage			-100	nA	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$
I_{DSS}	Zero Gate Voltage Drain Current			-50	μA	$V_{GS} = 0\text{V}, V_{DS} = \text{Max Rating}$
				-5	mA	$V_{GS} = 0\text{V}, V_{DS} = 0.8 \text{ Max Rating}$ $T_A = 125^\circ\text{C}$
$I_{D(ON)}$	ON-State Drain Current	-1.0			A	$V_{GS} = -5\text{V}, V_{DS} = -25\text{V}$
		-5.0				$V_{GS} = -10\text{V}, V_{DS} = -25\text{V}$
$R_{DS(ON)}$	Static Drain-to-Source ON-State Resistance		1.7	5	Ω	$V_{GS} = -5\text{V}, I_D = -0.5\text{A}$
			1.5	2		$V_{GS} = -10\text{V}, I_D = -2.0\text{A}$
$\Delta R_{DS(ON)}$	Change in $R_{DS(ON)}$ with Temperature		0.7	1.0	%/°C	$I_D = -1.0\text{A}, V_{GS} = -10\text{V}$
G_{FS}	Forward Transconductance	0.9	1.3		\bar{U}	$V_{DS} = -25\text{V}, I_D = -2.0\text{A}$
C_{ISS}	Input Capacitance		300	350	pF	$V_{GS} = 0\text{V}, V_{DS} = -25\text{V}$ $f = 1 \text{ MHz}$
C_{OSS}	Common Source Output Capacitance		125	150		
C_{RSS}	Reverse Transfer Capacitance		20	35		
$t_{d(ON)}$	Turn-ON Delay Time		35	40	ns	$V_{DD} = -25\text{V}$ $I_D = -2.0\text{A}$ $R_{GEN} = 10\Omega$
t_r	Rise Time		20	30		
$t_{d(OFF)}$	Turn-OFF Delay Time		40	50		
t_f	Fall Time		10	20		
V_{SD}	Diode Forward Voltage Drop		-1.4	-2.5		
t_{rr}	Reverse Recovery Time		400		ns	$I_{SD} = -1.0\text{A}, V_{GS} = 0\text{V}$

Notes:

- All D.C. parameters 100% tested at 25°C unless otherwise stated. (Pulse test: 300 μs pulse, 2% duty cycle.)
- All A.C. parameters sample tested.

Switching Waveforms and Test Circuit

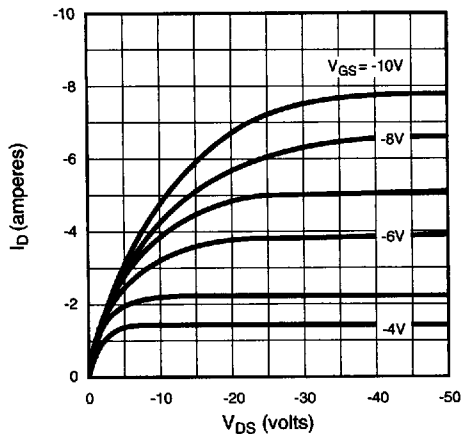


Typical Performance Curves

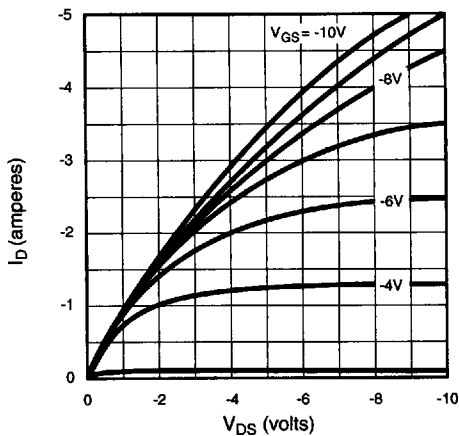
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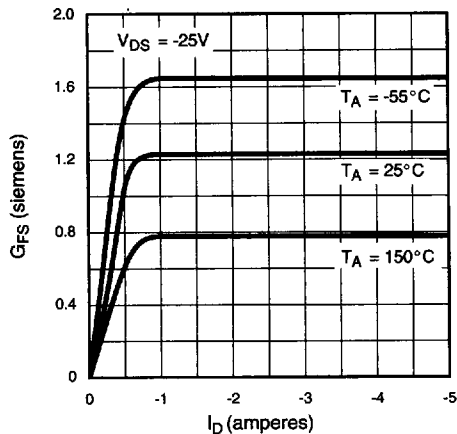
Output Characteristics



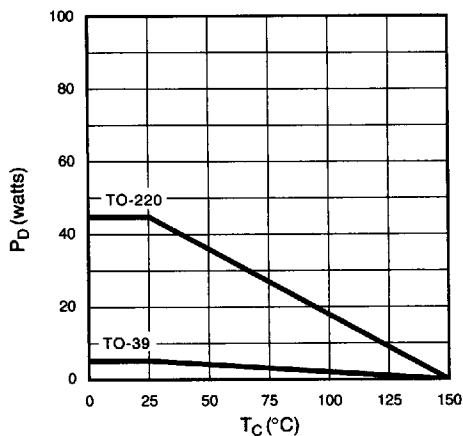
Saturation Characteristics



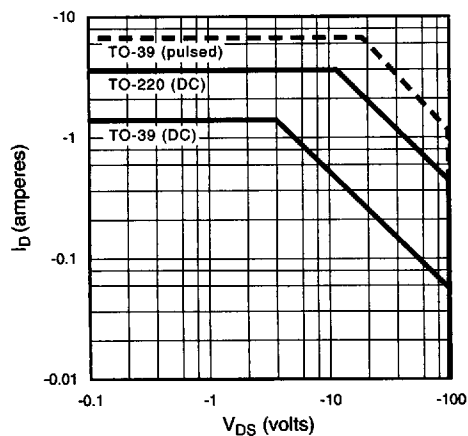
Transconductance vs. Drain Current



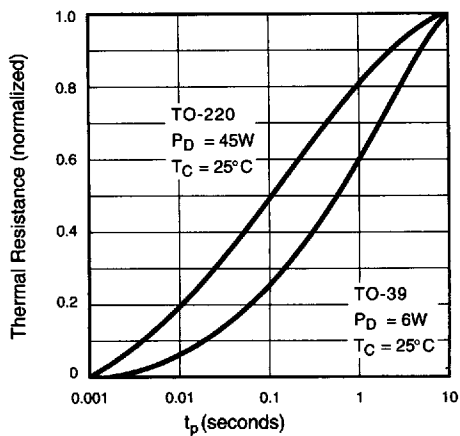
Power Dissipation vs. Case Temperature



Maximum Rated Safe Operating Area



Thermal Response Characteristics

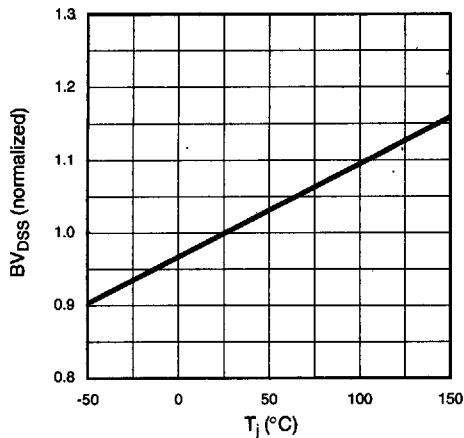


Typical Performance Curves

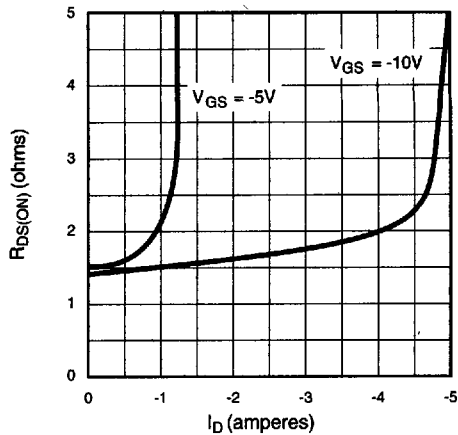
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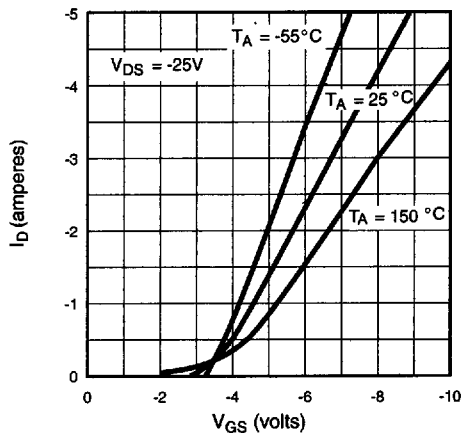
BV_{DSS} Variation with Temperature



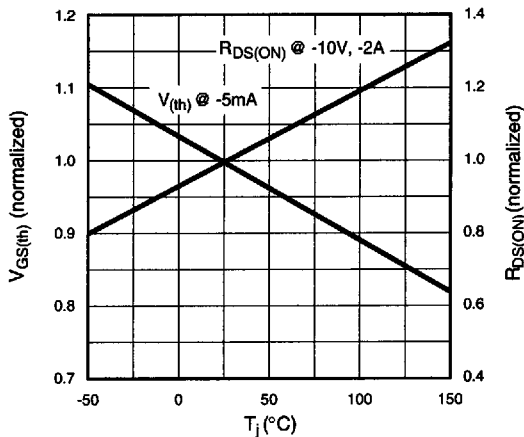
On-Resistance vs. Drain Current



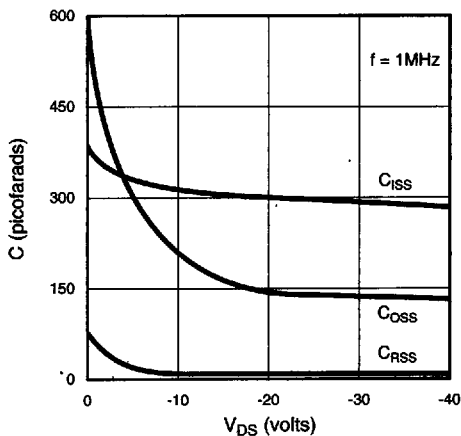
Transfer Characteristics



V_(th) and R_{DS} Variation with Temperature



Capacitance vs. Drain-to-Source Voltage



Gate Drive Dynamic Characteristics

